

# Photo Transistor --ORT-PT3246L

## 1. Scope:

- This specification applies to NPN silicon photo transistor chips.

## 2. Structure:

- Electrodes:  
Base : aluminium alloy  
Emitter : aluminium alloy  
Collector: Silver alloy

## 3. Size:

- Die Size : (1168 $\mu$ m $\times$ 1168 $\mu$ m)  $\pm$ 40 $\mu$ m
- Thickness : 220 $\mu$ m $\pm$ 38 $\mu$ m
- Pad Size:  
● Base : (117 $\mu$ m $\times$ 117 $\mu$ m)  $\pm$ 10 $\mu$ m  
● Emitter : (124 $\mu$ m $\times$ 124 $\mu$ m)  $\pm$ 10 $\mu$ m  
● Active Area : (787 $\mu$ m $\times$ 787 $\mu$ m)  $\pm$ 10 $\mu$ m  
● Pattern Drawing: fig.1.

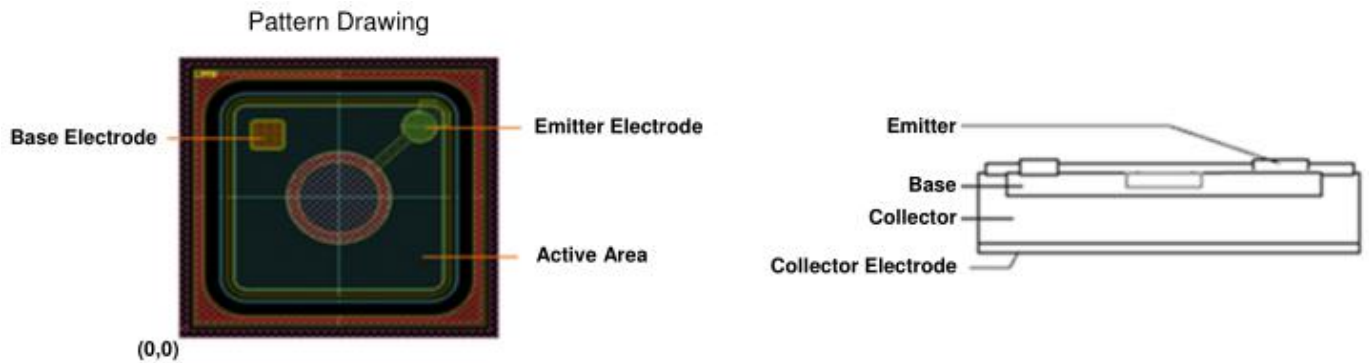


fig.1

## 4. Electro-Optical Characteristics:

( $T_a=+25^{\circ}\text{C}$ )

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
C-E Leakage Current	$I_{CEO}$	$V_{CE}=200\text{V}$	-	-	50	nA
C-E Saturation Voltage	$V_{CES}$	$I_C=1\text{mA}, I_B=15\mu\text{A}$	-	-	300	mV
C-E Voltage	$BV_{CEO}$	$I_C=0.1\text{mA}$	350	-	-	V
E-C Voltage	$BV_{ECO}$	$I_E=100\mu\text{A}$	8	-	20	V
DC Current Gain	$h_{FE}$	$V_{CE}=5\text{V}, I_C=2\text{mA}$	120	-	240	-



## 5. Packing :

- Packing: Sheet Type

## 6. Application Notes:

- All data are measured by Orient's tester on bare chips within 98% of the nominal value.